ABSTRACT

There is provided an etching method for etching an object to be processed by using a substrate processing apparatus including a process chamber including a first electrode and a second electrode disposed opposite to the first electrode to receive the object to be processed thereon. The etching method includes a process of removing at least one of a first polymer and a second polymer by etching the object to be processed on which a pattern of the first polymer and the second polymer is formed by phase separation of a block copolymer containing the first polymer and the second polymer at a temperature lower than or equal to 10 degrees C by using plasma of a process gas.

Fig. 2B